

WE CLAIM:

1. A method of removing a resist from a substrate by contacting a substrate having a resist thereon with an aqueous remover wherein said remover contains hydroxylamine and at least one alkanolamine wherein said hydroxylamine and said alkanolamine are present in sufficient amounts to remove a resist from a substrate.

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2. The method of claim 1 wherein the resist includes a polyimide.

3. The method of claim 1 wherein the resist includes resist that has been exposed to a process selected from plasma etching, reactive ion etching and ion milling.

4. The method of claim 1 wherein said remover further includes a chelating agent.

5. The method of claim 1 wherein said hydroxylamine and said solvent are maintained separately and are combined at the process location where said remover contacts said resist.

6. The method of claim 5 wherein a chelating agent is added to the remover after combining said hydroxylamine and said alkanolamine.

7. The method of claim 1 wherein said remover contacts said resist during the fabrication of a submicron integrated circuit.

8. The method of claim 1 wherein said hydroxylamine is present in an amount from at least about 2.5% to about 45% by weight neat.

9. The method of claim 8 wherein said remover further contains a chelating agent.

10. The method of claim 9 wherein said remover further contains at least one polar solvent.

11. The method of claim 8 wherein said at least one alkanolamine is selected from the group consisting of monoamines, diamines and triamines.

12. A method of removing a resist from a substrate by contacting a substrate having a resist thereon with an aqueous remover wherein said remover comprises from about 2.5% to about 45% by weight neat hydroxylamine, at least one alkanolamine, and at least one polar solvent wherein said remover contacts said substrate having a resist thereon after a process of etching.

13. The method of claim 12 wherein said contacting occurs after the process of etching.

14. The method of claim 1 wherein the aqueous remover contains at least about 70% water.

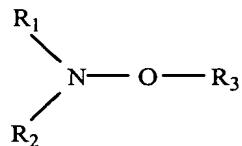
15. The method of claim 12 wherein the aqueous remover contains at least about 70% water.

16. The method of claim 12 wherein said remover further includes a chelating agent.

17. The method of claim 4 wherein said chelating agent is an organic acid.

18. The method of claim 16 wherein said chelating agent is an organic acid.

19. A method of removing a resist from a substrate by contacting a substrate having a resist thereon with an aqueous remover wherein said remover comprises a hydroxylamine of the formula:



5 wherein R₁, R₂, and R₃ are independently hydrogen; a hydroxyl group; optionally a substituted C₁-C₆ straight, branched or cyclo alkyl, alkenyl, or alkynyl group; optionally a substituted acyl group, straight or branched alkoxy group, amidyl group, carboxyl group, alkoxyalkyl group, alkylamino group, alkylsulfonyl group, or sulfonic acid group, or the

10 salt of such compounds; at least one alkanolamine selected from the group consisting of monoamines, diamines and triamines; at least one polar solvent; and at least one chelating agent.

20. The method of claim 19 wherein said contacting occurs after the process of etching.